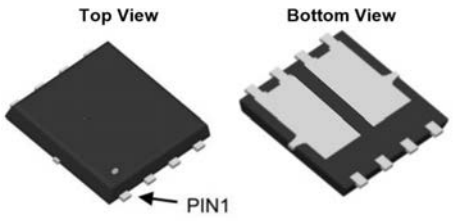
Features

- N-Channel: 30V, 18A
  $R_{DS(ON)}$***TYP*** = 10mΩ @ V_{GS} = 10V
  $R_{DS(ON)}$***TYP*** = 17mΩ @ V_{GS} = 4.5V
- P-Channel: -30V, -16A
  $R_{DS(ON)}$***TYP*** = 20mΩ @ V_{GS} = -10V
  $R_{DS(ON)}$***TYP*** = 33mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

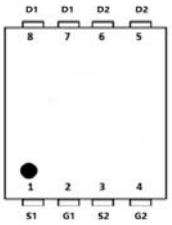
100% UIS TESTED!
100% ΔVds TESTED!



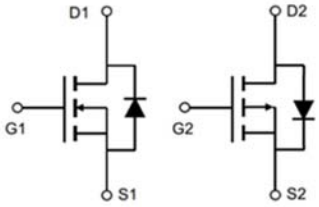
PDFN3x3-8L-D

Application

- Battery Protection
- Load Switch
- Power Management



Pin Assignment



Schematic Diagram

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max. N-Channel	Max. P-Channel	Units
V_{DSS}	Drain-Source Voltage		30	-30	V
V_{GSS}	Gate-Source Voltage		±20	±20	V
I_D	Continuous Drain Current	T_C = 25℃	18	-16	A
		T_C= 100℃	10.8	-9.6	A
I_{DM}	Pulsed Drain Current note1		72	-64	A
E_{AS}	Single Pulsed Avalanche Energy note2		30	30	mJ
P_D	Power Dissipation	T_C= 25℃	13.8	13.8	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		9	9	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		℃

N-Channel Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.6	2.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS}=10V, I_D=5A	-	10	13	mΩ
		V_{GS}=4.5V, I_D=3A	-	17	20	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1.0MHz	-	778	-	pF
C_{oss}	Output Capacitance		-	105	-	pF
C_{rss}	Reverse Transfer Capacitance		-	85	-	pF
Q_g	Total Gate Charge	V_{DS}=15V, I_D=5A, V_{GS}=10V	-	15	-	nC
Q_{gs}	Gate-Source Charge		-	4	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	3.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=15V, I_D=10A, V_{GS}=10V, R_{REN} =3Ω	-	7	-	ns
t_r	Turn-on Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	16	-	ns
t_f	Turn-off Fall Time		-	5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	18	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	72	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=10A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25℃, V_{DD}=15V, V_{GS}=10V, L=0.5mH, Rg=25Ω, I_{AS}=11A

   T_J=25℃, V_{DD}= -15V, V_{GS}= -10V, L=0.5mH, Rg=25Ω, I_{AS}= -11A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

P-Channel Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -30V, V_{GS}=0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.1	-1.6	-2.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -5A	-	20	26	mΩ
		V_{GS}= -4.5V, I_D= -3A	-	33	43	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -15V, V_{GS}=0V, f=1.0MHz	-	643	-	pF
C_{oss}	Output Capacitance		-	109	-	pF
C_{rss}	Reverse Transfer Capacitance		-	93	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D= -5.0A, V_{GS}= -10V	-	52	-	nC
Q_{gs}	Gate-Source Charge		-	9	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -15V, I_D= -5A, V_{GS}= -10V, R_{GEN}=6Ω	-	14	-	ns
t_r	Turn-on Rise Time		-	16	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	200	-	ns
t_f	Turn-off Fall Time		-	99	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-16	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-64	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -10A	-	-	-1.2	V

Test Circuit-N

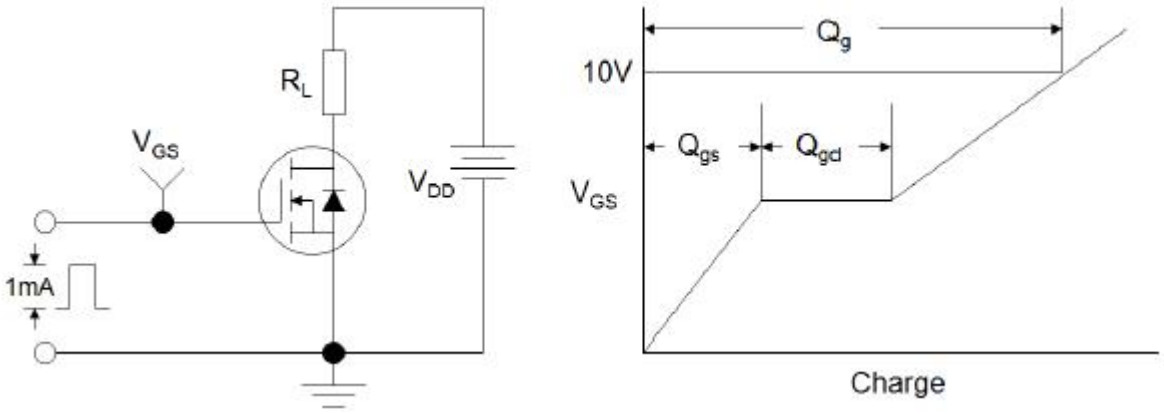


Figure1:Gate Charge Test Circuit & Waveform

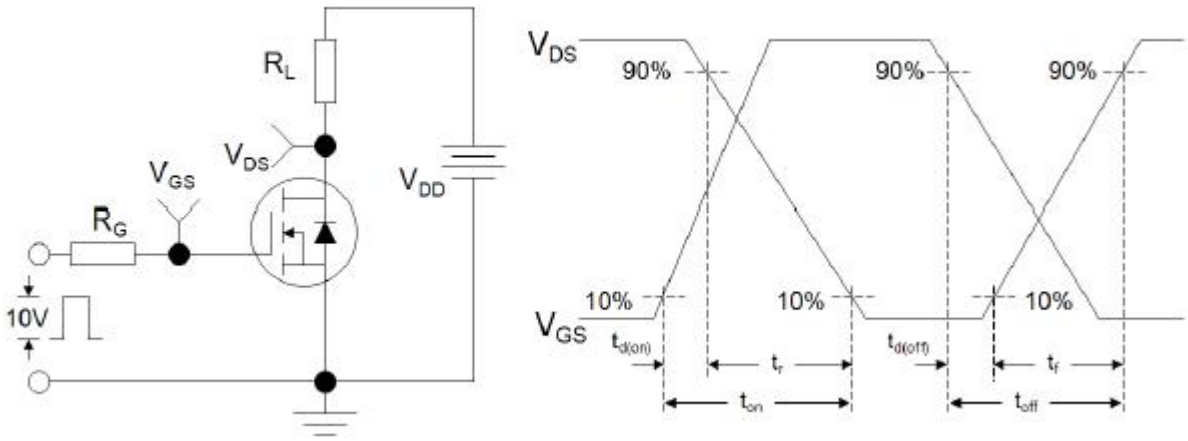


Figure 2: Resistive Switching Test Circuit & Waveforms

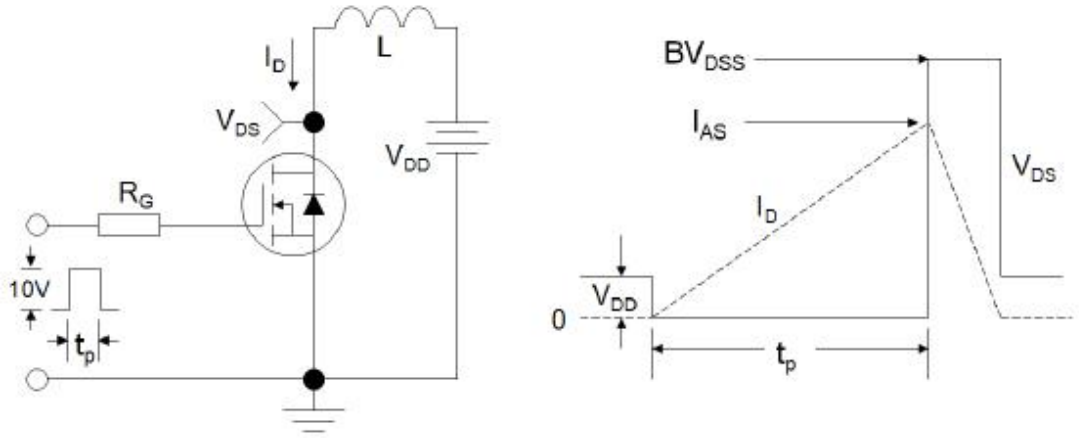
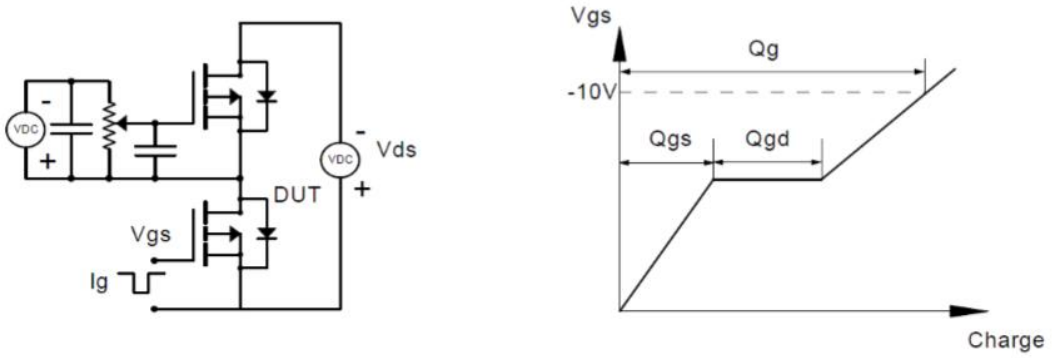


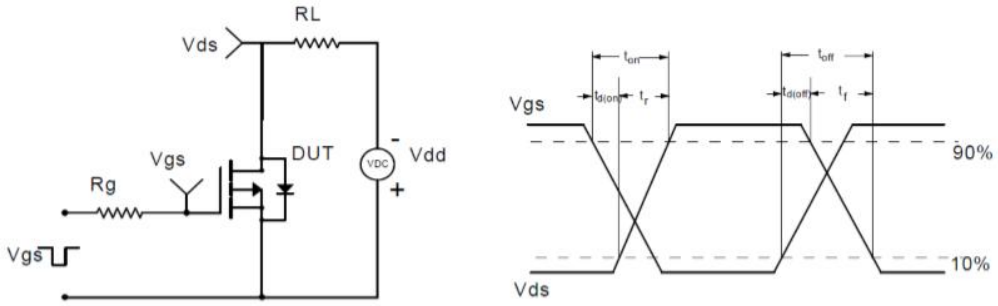
Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Test Circuit-P

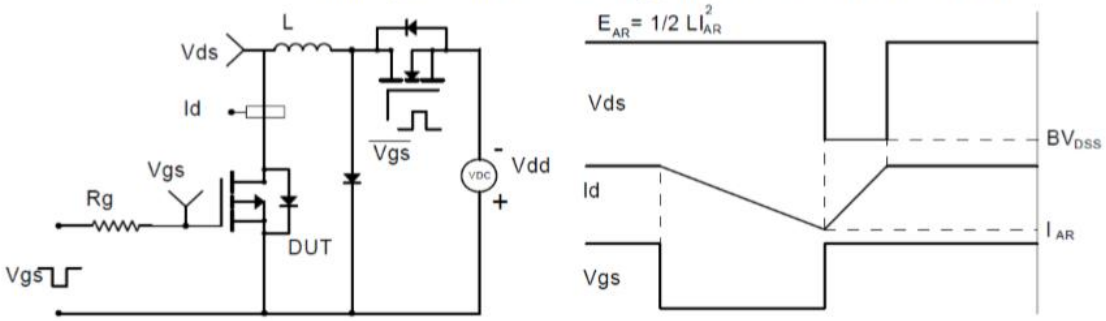
Gate Charge Test Circuit & Waveform



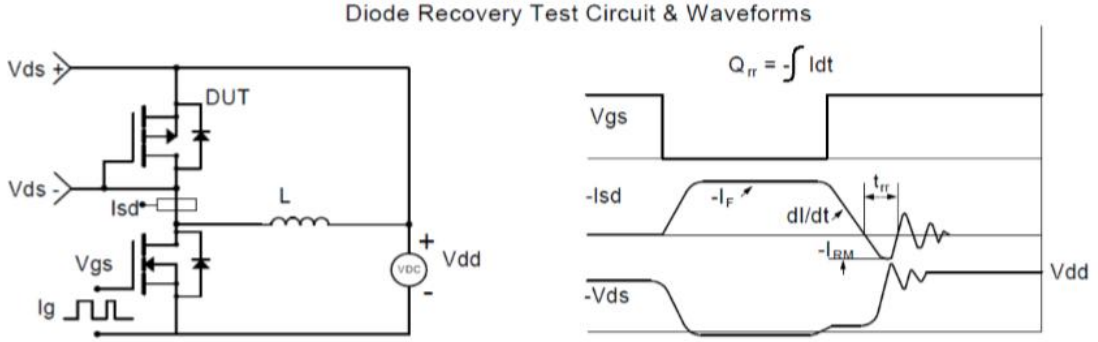
Resistive Switching Test Circuit & Waveforms



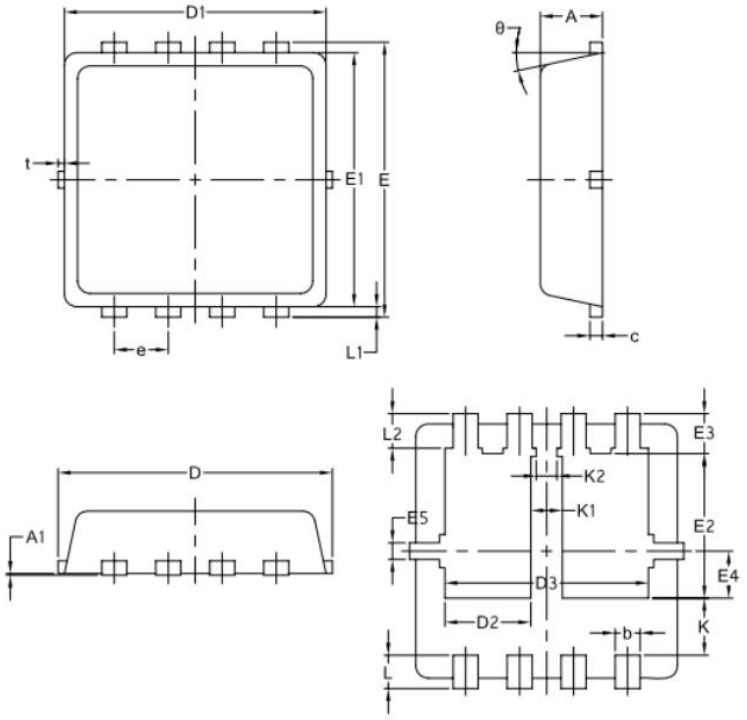
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

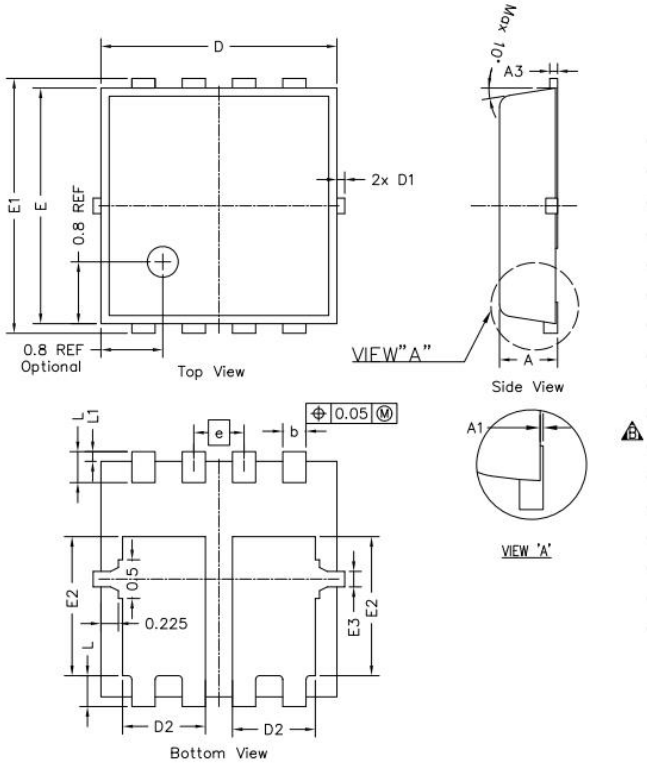


Package Mechanical Data-PDFN3x3-8L-D-Type A



SYMBOL	COMMON		
	MM		
	MIN	NOM	MAX
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
θ	10°	12°	14°

Package Mechanical Data-PDFN3x3-8L-D-Type B



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
A3	0.144	0.152	0.202	0.006	0.006	0.008
b	0.250	0.300	0.350	0.010	0.012	0.014
e	0.65 BSC			0.026 BSC		
D	2.950	3.050	3.150	0.116	0.120	0.124
E	2.950	3.050	3.150	0.116	0.120	0.124
D1	---	---	0.125	----	----	0.005
E1	3.200	3.300	3.400	0.126	0.130	0.134
D2	0.970	1.070	1.170	0.038	0.042	0.046
E2	1.700	1.800	1.900	0.067	0.071	0.075
E3	0.150	0.200	0.250	0.006	0.008	0.010
L	0.300	0.400	0.500	0.012	0.016	0.020
L1	0.075	0.125	0.175	0.003	0.005	0.007